### Thyristors Datasheet

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# MAC228A Sensitive Gate Triacs – 400V - 800V



## **Additional Information**



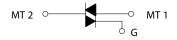




Resources

Accessories

### **Functional Diagram**



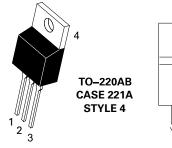
## Description

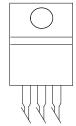
Designed primarily for industrial and consumer applications for full–wave control of AC loads such as appliance controls, heater controls, motor controls, and other power switching applications.

### **Features**

- Sensitive Gate Triggering in 3 Modes for AC Triggering on Sinking Current Sources
- Four Mode Triggering for Drive Circuits that Source Current
- All Diffused and Glass– Passivated Junctions for Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance and High Heat Dissipation
- Center Gate Geometry for Uniform Current Spreading
- These Devices are Pb–Free and are RoHS Compliant









<b>Maximum Ratings</b> ( $T_J = 25^{\circ}C$ unless otherwise noted)						
Rating	Symbol	Value	Unit			
Peak Repetitive Off–State Voltage (Note 1) (T <sub>J</sub> =-40 to 110°C, Sine Wave, 50 to 60 Hz, Gate Open)	MAC228A4 MAC228A6 MAC228A8 MAC228A10	V <sub>drm</sub> , V <sub>rrm</sub>	200 400 600 800	V		
On-State RMS Current ( $T_c = 80^{\circ}$ C) Full Cycle Sine Wave, 50 to	60 Hz	I <sub>T (RMS)</sub>	8.0	А		
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, TJ = 110°C)	I <sub>TSM</sub>	80	А			
Circuit Fusing Consideration ( $t = 8.3 \text{ ms}$ )	l²t	26	A <sup>2</sup> sec			
Peak Gate Current, (t $\leq$ 2 µs, T <sub>c</sub> = 80°C)	I <sub>GM</sub>	±2.0	А			
Peak Gate Voltage, (t $\leq$ 2 µs, TC = 80°C)	V <sub>GM</sub>	±10	V			
Peak Gate Power (t $\leq$ 2 $\mu s, T_{_C}$ = 80°C)	P <sub>GM</sub>	20	W			
Average Gate Power (t $\leq$ 8.3 ms, T <sub>c</sub> = 80°C)	P <sub>G (AV)</sub>	0.5	W			
Operating Junction Temperature Range	TJ	-40 to +110	°C			
Storage Temperature Range		T <sub>stg</sub>	-40 to +150	°C		
Mounting Torque		_	8.0	in Ib		

## Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

V Used and V<sub>BML</sub> for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

Thermal Characteristics	Therma	Chara	cteristics
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Rating		Symbol	Value	Unit
Thermal Resistance,	Junction-to-Case (AC) Junction-to-Ambient	R <sub>ejc</sub> R <sub>eja</sub>	2.0 62.5	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds		TL	260	°C

## **Electrical Characteristics - OFF** ( $T_J = 25^{\circ}C$ unless otherwise noted ; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak Repetitive Blocking Current	T_ = 25°C	I <sub>DRM</sub> ,	-	-	10	μΑ
$(V_{D} = V_{DRM} = V_{RRM}; \text{ Gate Open})$	T_ = 110°C	I	-	-	2.0	mA

### **Electrical Characteristics - ON** (T<sub>J</sub> = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Мах	Unit
Peak On–State Voltage ( $I_{TM} = \pm 11$ A Peak, Pulse Width $\leq 2$ ms, Duty Cycle $\leq 2\%$ )		V <sub>TM</sub>	-	_	1.8	V
	MT2(+), G(+)		_	-	5.0	
Gate Trigger Current (Continuous dc)	MT2(+), G(-)		_	_	5.0	~^^
$(V_{p} = 12 \text{ V}, \text{ R}_{1} = 100 \Omega)$	MT2(-), G(-)	I <sub>GT</sub>	_	-	5.0	mA
	MT2(-), G(+)		_	-	10	
	MT2(+), G(+)		_	_	2.0	
Gate Trigger Voltage	MT2(+), G(-)	V	_	-	2.0	V
(Continuous dc) ( $V_p = 12 V, R_1 = 100 \Omega$ )	MT2(-), G(-)	V <sub>GT</sub>	_	_	2.0	V
	MT2(-), G(+)		_	-	2.5	
Gate Non–Trigger Voltage (Continuous DC), (V $_{\rm D}$ = 12 V, T $_{\rm C}$ = 110°C, R $_{\rm L}$ = 100 $\Omega$ ) All Four Quadrants		$V_{\rm GD}$	0.2	_	-	V
Holding Current ( $V_{D} = 12 V_{dc}$ , Gate Open, Initiating Current = ±200 mA))		I <sub>H</sub>	_	-	15	mA
Gate–Controlled Turn–On Time, ( $V_{D}$ = Rated $V_{DRM}$ , $I_{TM}$ = 16 A Peak, $I_{G}$ = 30 mA)		t <sub>gt</sub>	_	1.5	_	μs

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#### **Dynamic Characteristics**

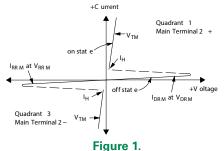
Characteristic	Symbol	Min	Тур	Мах	Unit
Critical Rate of Rise of Commutation Voltage ( $V_D = Rated V_{DRM'}  _{TM} = 11.3 A$ , Commutating di/dt = 4.1 A/ms, Gate Unenergized, $T_C = 80$ °C)	di/dt <sub>(c)</sub>	_	5.0	-	V/µs
Critical Rate of Rise of Off-State Voltage ( $V_D = Rated V_{DRM}$ , Exponential Waveform, Gate Open, $T_C = 110^{\circ}C$ )	dv/dt	_	25	_	V/µs

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

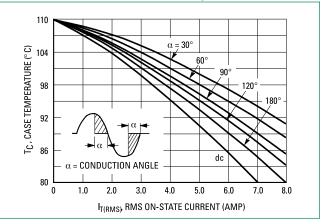
## **Voltage Current Characteristic of SCR**

Symbol	Parameter
V <sub>drm</sub>	Peak Repetitive Forward Off State Voltage
I <sub>DRM</sub>	Peak Forward Blocking Current
V <sub>RRM</sub>	Peak Repetitive Reverse Off State Voltage
I <sub>BRM</sub>	Peak Reverse Blocking Current
V <sub>TM</sub>	Maximum On State Voltage
I <sub>H</sub>	Holding Current

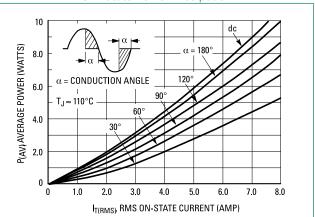
**Quadrant Definitions for a Triac** 







#### **Figure 2.** On–State Power Dissipation



#### MT2 POSITIVE (Positive Half Cycle) (+) MT 2 (+) MT 2 Quadrant II (<del>\_</del>) I<sub>GT</sub> GA TE Quadrant I (+) I<sub>GT</sub> GATE 0 0 ф мт 1 ό MT 1 RE F RE F +I GT IGT (-) MT 2 (<del>-</del>) MT 2 Quadrant IV Quadrant III (+) I<sub>GT</sub> (<del>-</del>) I<sub>GT</sub> GA TE 0 MT 1 RE F RE F MT2 NEGA TIVE (Negative Half Cycle)

All polarities are referenced to MT1.

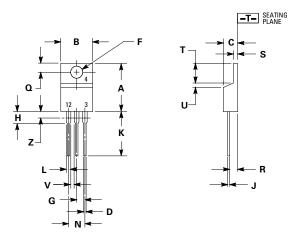
With in-phase signals (using standard AC lines) quadrants I and III are used



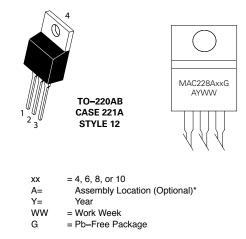
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#### **Dimensions**



#### **Part Marking System**



Dim	Inches		Millin	neters
DIM	Min	Мах	Min	Max
Α	0.590	0.620	14.99	15.75
В	0.380	0.420	9.65	10.67
С	0.178	0.188	4.52	4.78
D	0.025	0.035	0.64	0.89
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.41	2.67
н	0.110	0.130	2.79	3.30
J	0.018	0.024	0.46	0.61
к	0.540	0.575	13.72	14.61
L	0.060	0.075	1.52	1.91
Ν	0.195	0.205	4.95	5.21
Q	0.105	0.115	2.67	2.92
R	0.085	0.095	2.16	2.41
S	0.045	0.060	1.14	1.52
т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045		1.15	
Z		0.080		2.04

Pin Assignment				
1	Main Terminal 1			
2	Main Terminal 2			
3	Gate			
4	Main Terminal 2			

#### **Ordering Information**

Device	Package	Shipping			
MAC228A4G					
MAC228A6G					
MAC228A6TG	TO-220AB	1000 Units/ Box			
MAC228A8G	(Pb-Free)	1000 UTIILS/ BOX			
MAC228A8TG					
MAC228A10G					

Dimensioning and tolerancing per ansi y14.5m, 1982.
Controlling dimension: inch.

3. Dimension z defines a zone where all body and lead irregularities are allowed.

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